

The Electrochemical Society

Nonvolatile Memory and Its Evolution

at the 214th ECS Meeting

ECS Transactions Volume 16 No.20

October 12-17, 2008
Honolulu, Hawaii, USA

Printed from e-media with permission by:

Curran Associates, Inc.
57 Morehouse Lane
Red Hook, NY 12571
www.proceedings.com

ISBN: 978-1-61567-294-3

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)

Printed in the United States of America.

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